





# **Phase Control Thyristor**

DS5812-3 January 2014 (LN31242)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR1570L65* DCR1570L60 DCR1570L55 DCR1570L50	6500 6000 5500 5000	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to } 125^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 300\text{mA}, \\ V_{DRM}, V_{RRM}  t_p &= 10\text{ms}, \\ V_{DSM}  \&  V_{RSM} &= \\ V_{DRM}  \&  V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. \* 6200V @ -40° C, 6500V @ 0° C

## **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

## DCR1570L65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### **KEY PARAMETERS**

$V_{DRM}$	6500V
$I_{T(AV)}$	1568A
I <sub>TSM</sub>	22000A
dV/dt*	1500V/µs
dI/dt	300A/μs

## \* Higher dV/dt selections available

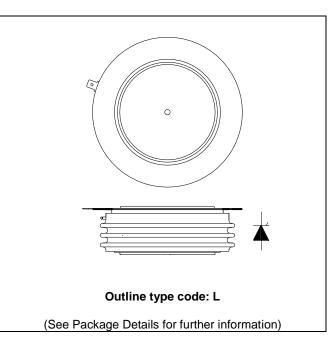


Fig. 1 Package outline





## **CURRENT RATINGS**

## $T_{\text{case}}$ = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	1570	А
I <sub>T(RMS)</sub>	RMS value	-	2466	Α
I <sub>T</sub>	Continuous (direct) on-state current	-	2340	А

## **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, T <sub>case</sub> = 125°C	22.0	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	2.42	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.0117	°C/W
		Single side cooled	Anode DC	-	0.0187	°C/W
			Cathode DC	-	0.0329	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 37kN	Double side	-	0.0025	°C/W
		(with mounting compound)	Single side	-	0.005	°C/W
T <sub>vj</sub>	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
F <sub>m</sub>	Clamping force			33	41	kN





# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	150	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	300	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
$V_{T(TO)}$	Threshold voltage – Low level	100A to 1500A at T <sub>case</sub> = 125	2°C	-	1.0	V
	Threshold voltage – High level	1500A to 7200A at T <sub>case</sub> = 125°C		-	1.2	V
r <sub>T</sub>	On-state slope resistance – Low level	100A to 1500A at T <sub>case</sub> = 125°C		-	0.615	mΩ
	On-state slope resistance – High level	1500A to 7200A at T <sub>case</sub> = 125°C		-	0.5	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, $10\Omega$		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 1$ A/ $\mu$ s,		-	1200	μs
		dV <sub>DR</sub> /dt = 20V/µs linear				
Qs	Stored charge	$I_T = 2000A$ , $T_j = 125$ °C, $dI/dt - 1A/\mu s$ ,		2000	4500	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	Α
I <sub>H</sub>	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_T = 5A$		-	300	mA





## **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	350	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	15	mA

## **CURVES**

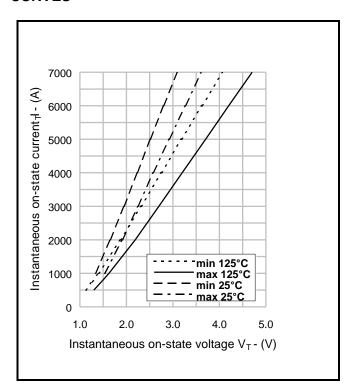


Fig.2 Maximum & minimum on-state characteristics

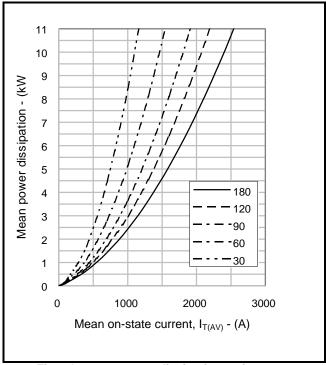
 $V_{TM}$  EQUATION Where A = 0.666848

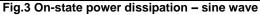
 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T} \\ B = 0.033446 \\ C = 0.000418$ 

D = 0.009666

these values are valid for  $T_j = 125$ °C for  $I_T 100$ A to 7200A







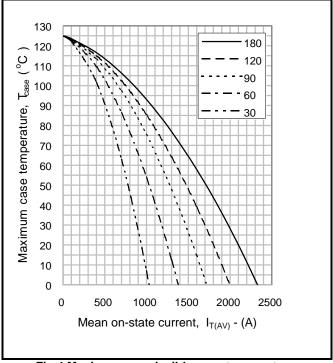


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

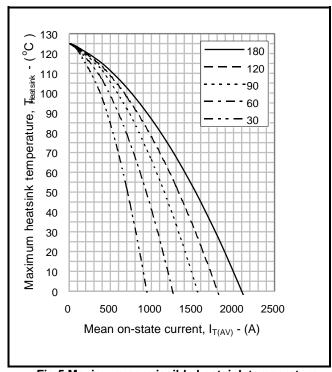


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

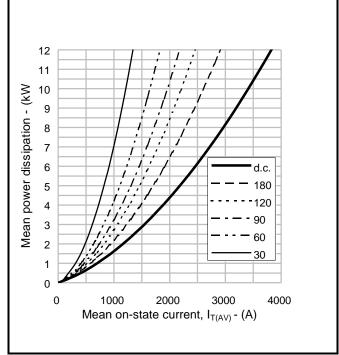
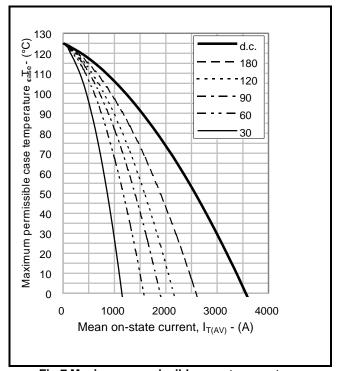
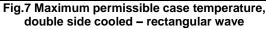


Fig.6 On-state power dissipation - rectangular wave







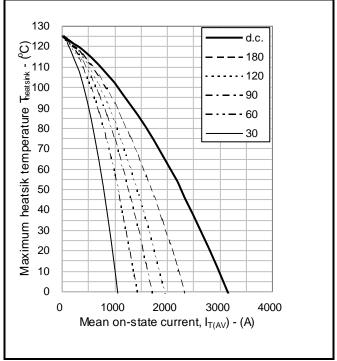


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave

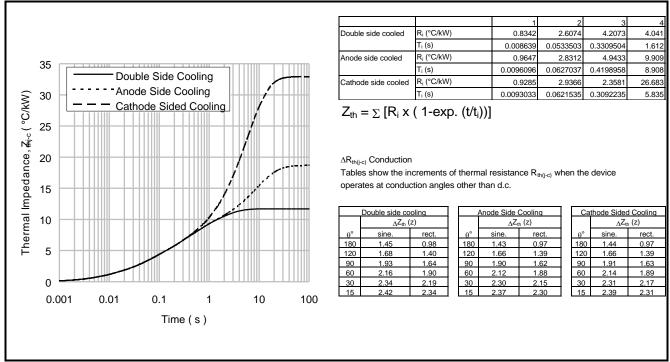
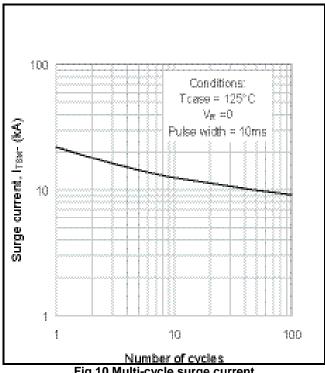


Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)







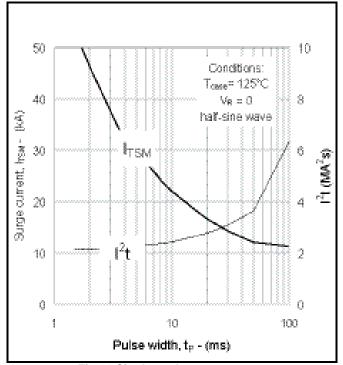


Fig.11 Single-cycle surge current

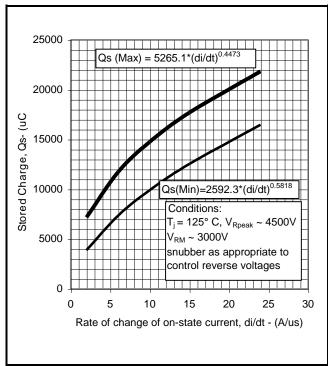


Fig.12 Reverse recovery charge

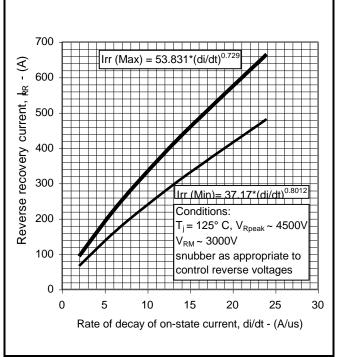


Fig.13 Reverse recovery current

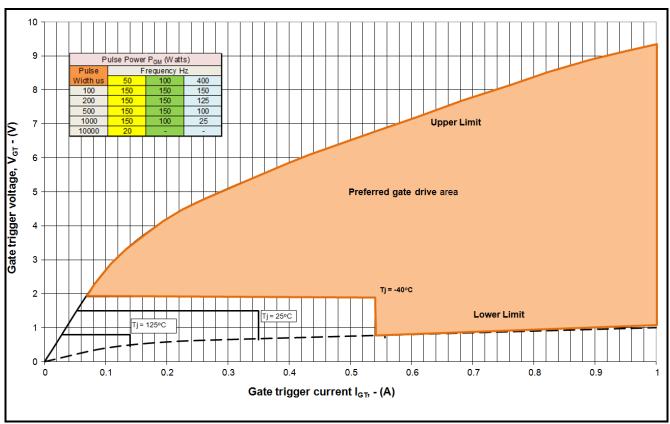


Fig14 Gate Characteristics

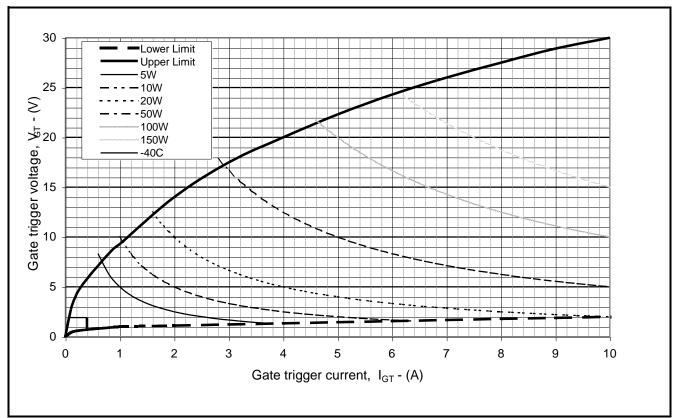


Fig. 15 Gate characteristics





## **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

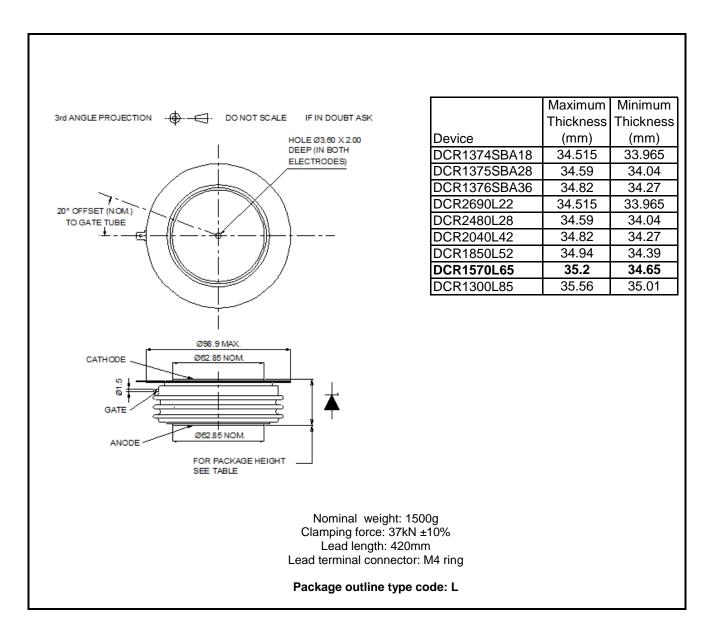


Fig.16 Package outline





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